

L Number	Hits	Search Text	DB	Time stamp
1	0	10/463219	USPAT	2004/05/05 09:21
2	0	10/187465	USPAT	2004/05/05 09:22
3	0	10/187466	USPAT	2004/05/05 09:22
4	0	10/187468	USPAT	2004/05/05 09:22
6	11	(initial adj film) and growth and annealing and heat and growing and thickness and silicon and nitride and oxide	USPAT	2004/05/05 10:08
5	7	(initial adj layer) and growth and annealing and heat and growing and thickness and silicon and nitride and oxide	USPAT	2004/05/05 09:39
7	1	("6610428").PN.	USPAT	2004/05/05 09:39
8	1	("6172009").PN.	USPAT	2004/05/05 09:39
9	1	(("6610428").PN.) and (epitaxial-or-growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 09:47
10	1	(("6172009").PN.) and (epitaxial or growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 09:50
11	1	("6246105").PN.	USPAT	2004/05/05 09:49
12	1	(("6246105").PN.) and (epitaxial or growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 10:41
13	1	("6217658").PN.	USPAT	2004/05/05 09:55
14	1	(("6217658").PN.) and (epitaxial or growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 10:28
15	1	("5492857").PN.	USPAT	2004/05/05 09:56
16	1	(("5492857").PN.) and (epitaxial or growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 09:56
17	4	(initial adj film) and (critical adj thickness)	USPAT	2004/05/05 10:21
18	4	((initial adj film) and (critical adj thickness)) and (epitaxial or growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 10:09
19	13	(Initial adj layer) and (critical adj thickness)	USPAT	2004/05/05 10:28
20	1	("6153894").PN.	USPAT	2004/05/05 10:28
21	1	(("6153894").PN.) and (epitaxial or growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 10:32
22	1	("6001669").PN.	USPAT	2004/05/05 10:32
23	1	(("6001669").PN.) and (epitaxial or growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 10:34
24	1	("5637530").PN.	USPAT	2004/05/05 10:34
25	1	(("5637530").PN.) and (epitaxial or growth or temperature or heat or anneal or annealing or growing or initial or layer or film or dimension or two or silicon or oxide or nitride or ZnO or AlN)	USPAT	2004/05/05 10:34
26	1	("6172009").PN.	USPAT	2004/05/05 10:41
27	1	("5492857").PN.	USPAT	2004/05/05 10:42
28	1	("6217658").PN.	USPAT	2004/05/05 10:43
29	1	("5830270").PN.	USPAT	2004/05/05 10:44
30	1	("5637530").PN.	USPAT	2004/05/05 10:44
31	1	("5442205").PN.	USPAT	2004/05/05 10:56
32	936	438/660	USPAT	2004/05/05 10:57

33	345	438/663	USPAT	2004/05/05 10:57
34	991	438/680	USPAT	2004/05/05 10:57
35	479	438/681	USPAT	2004/05/05 10:57
36	644	438/743	USPAT	2004/05/05 10:58
37	366	438/744	USPAT	2004/05/05 10:58
38	150	438/954	USPAT	2004/05/05 10:58
39	236	438/933	USPAT	2004/05/05 10:58

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